

**66177**

**GULL WING HERMETICALLY SEALED,  
SINGLE CHANNEL OPTOCOUPLER  
(Electrically Similar To 4N47, 4N48, 4N49)**

**Mii**  
OPTOELECTRONIC  
PRODUCTS  
DIVISION

REV A 5/7/01

**Features:**

- High Reliability
- Base lead provided for conventional transistor biasing
- Very high gain, high voltage transistor
- Stability over wide temperature range.
- High voltage electrical isolation

**Applications:**

- Eliminate ground loops
- Level shifting
- Line receiver
- Switching power supplies
- Motor control

**DESCRIPTION**

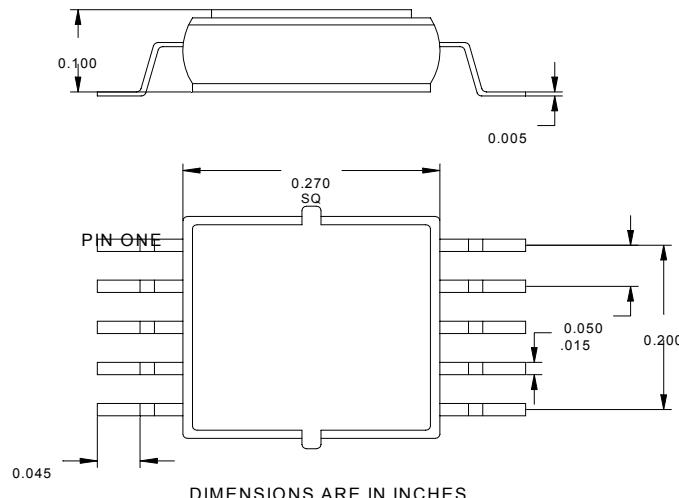
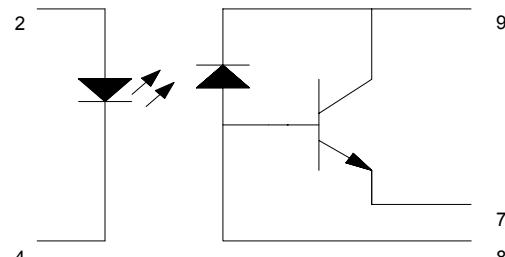
The **66177** single channel optocoupler consists of an LED optically coupled to a high gain silicon phototransistor. The 66177 is electrically equivalent to the 4N47 (-X01), 4N48 (-X02) and the 4N49 (-X03) and is available in standard and screened versions.

**ABSOLUTE MAXIMUM RATINGS**

Storage Temperature.....	-65°C to +150°C
Operating Free-Air Temperature Range .....	-55°C to +125°C
Lead Solder Temperature(10 seconds maximum) .....	240°C
Peak Forward Input Current .....	40mA (1ms duration)
Input Diode Continuous Forward Current at (or below) 65°C Free-Air Temperature (see note 2) .....	20mA
Input Power Dissipation .....	35mW
Reverse Input Voltage .....	2V
Collector-Base Voltage .....	45V
Collector-Emitter Voltage (See note 1).....	40V
Emitter-Base Voltage .....	7V
Continuous Collector Current .....	50mA
Continuous Transistor Power Dissipation at (or below) 25°C Free-Air Temperature (see Note 3) .....	300mW

**Notes:**

1. This value applies with the emitter-base diode open-circuited and the input-diode current equal to zero.
2. Derate linearly to 125°C free-air temperature at the rate of 0.2mA/°C.
3. Derate linearly to 125°C free-air temperature at the rate of 3mW/°C.

**Package Dimensions****Schematic Diagram**

66177

**GULL WING HERMETICLLY SEALED, SINGLE CHANNEL OPTOCOUPLER**  
**ELECTRICALLY SIMILAR TO 4N47, 4N48, 4N49**

REV A 5/7/01

**ELECTRICAL CHARACTERISTICS** $T_A = -55^\circ C$  to  $125^\circ C$  unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Input Diode Static Reverse Current	$I_R$			100	$\mu A$	$V_R = 2V$	
Input Diode Static Forward Voltage	$V_F$						
-55°C			1.0	1.7	V		
+25°C			0.8	1.4	V	$I_F = 10mA$	
+125°C			0.7	1.3	V		
Input to Output Resistance	$R_{IO}$	$10^{11}$			$\Omega$	$V_{IN-OUT} = 1kV$	
Input to Output Capacitance	$C_{IO}$		2.5	5	pF	$f = 1MHz, V_{IN-OUT} = 0$	1
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$			0.3	V	$I_F = 2mA, I_C = 0.5mA, I_B = 0$	
66177-X01							
66177-X02				0.3	V	$I_F = 2mA, I_C = 1mA, I_B = 0$	
66177-X03				0.3	V	$I_F = 2mA, I_C = 2mA, I_B = 0$	

**TYPICAL CHARACTERISTICS**AT  $T_A = 25^\circ C$ ,  $V_{CC} = 5V$  Each Channel

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	45			V	$I_C = 100\mu A, I_B = 0, I_F = 0$	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40			V	$I_C = 1mA, I_B = 0, I_F = 0$	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7			V	$I_C = 0mA, I_E = 100\mu A, I_F = 0$	
On State Collector Current	$I_{C(ON)}$	0.5		-			
66177-X01		1.0		5	mA	$V_{CE} = 5V, I_B = 0, I_F = 1mA$	
66177-X02		2.0		10			
66177-X03							
On State Collector Current	$I_{C(ON)}$	0.7			mA		
66177-X01		1.4				$V_{CE} = 5V, I_B = 0, I_F = 2mA$	
$T_a = -55^\circ C$		2.8					
66177-X02							
66177-X03							
On State Collector Current	$I_{C(ON)}$	0.5			mA		
66177-X01		1.0				$V_{CE} = 5V, I_B = 0, I_F = 2mA$	2
$T_a = +125^\circ C$		2.0					
66177-X02							
66177-X03							
Off State Collector Current	$I_{C(OFF)}$			100	nA	$V_{CE} = 20V, I_B = 0, I_F = 0mA$	
Off State Collector Current, $T_a = 125^\circ C$	$I_{C(OFF)}$			100	$\mu A$	$V_{CE} = 20V, I_B = 0, I_F = 0mA$	
Rise Time (Phototransistor Operation)	$t_r$		10	20			
or			10	25	$\mu s$	$V_{CC} = 10V, I_B = 0,$	
Fall Time	$t_f$		10	25		$I_F = 5mA, R_L = 100\Omega$	
66177-X01							
Rise Time (Photodiode Operation)	$t_r$		0.85	3	$\mu s$		
or			0.85	3		$V_{CC} = 10V, I_E = 0,$	
Fall Time	$t_f$		0.85	3		$I_F = 5mA, R_L = 100\Omega$	
66177-X02							
66177-X03							

**NOTES:**

- These parameters are measured between all phototransistor leads shorted together and with both input diode leads shorted together.
- This parameter must be measured using pulse techniques  $t_W = 100\mu s$ , duty cycle  $\leq 1\%$ .

**RECOMMENDED OPERATING CONDITIONS:**

PARAMETERS	SYMBOL	MIN	MAX	UNITS
Input Current, Low Level	$I_{FL}$	0	100	$\mu A$
Input Current, High Level	$I_{FH}$	1	2	mA
Supply Voltage	$V_{CC}$	5.0	20	V
Operating Temperature	$T_A$	-55	125	$^\circ C$

**SELECTION GUIDE**

PART NUMBER	PART DESCRIPTION
66177-001	Single Channel (4N47) optocoupler, Commercial
66177-101	Single Channel (4N47) optocoupler, full mil-temp (-55° to +125° C) with 100% device screening
66177-201	Single Channel (4N47) optocoupler, military operating range (-55° to +125° C)
66177-301	Single Channel (4N47) optocoupler, extended temperature range (-40° to +85° C)
66177-002	Single Channel (4N48) optocoupler, Commercial
66177-102	Single Channel (4N48) optocoupler, full mil-temp (-55° to +125° C) with 100% device screening
66177-202	Single Channel (4N48) optocoupler, military operating range (-55° to +125° C)
66177-302	Single Channel (4N48) optocoupler, extended temperature range (-40° to +85° C)
66177-003	Single Channel (4N49) optocoupler, Commercial
66177-103	Single Channel (4N49) optocoupler, full mil-temp (-55° to +125° C) with 100% device screening
66177-203	Single Channel (4N49) optocoupler, military operating range (-55° to +125° C)
66177-303	Single Channel (4N49) optocoupler, extended temperature range (-40° to +85° C)